

ABSTRACT OF THE INVENTION

The present invention relates to a ferroelectric polymer storage device including at least two stacked ferroelectric polymer memory structures that are arrayed next to at least two respective stacked topologies that are a pre-fabricated silicon substrate cavity that includes interlayer dielectric layers and via structures. Combining ferroelectric polymer and ferroelectric oxide layers on the pre-fabricated silicon substrate cavity forms a multi-rank structure.

"Express Mail" mailing label number: EL873859769US
Date of Deposit: September 21, 2001
This paper or fee is being deposited on the date indicated above with the United States Postal Service pursuant to 37 CFR 1.10, and is addressed to the Commissioner for Patents, Box Patent Application, Washington, D.C. 20231.
